SOT-23 ꞑ NPN Silicon NPN transistor in a SOT-23 Plastic Package.

1 ESD 4kV, 400V ǘ

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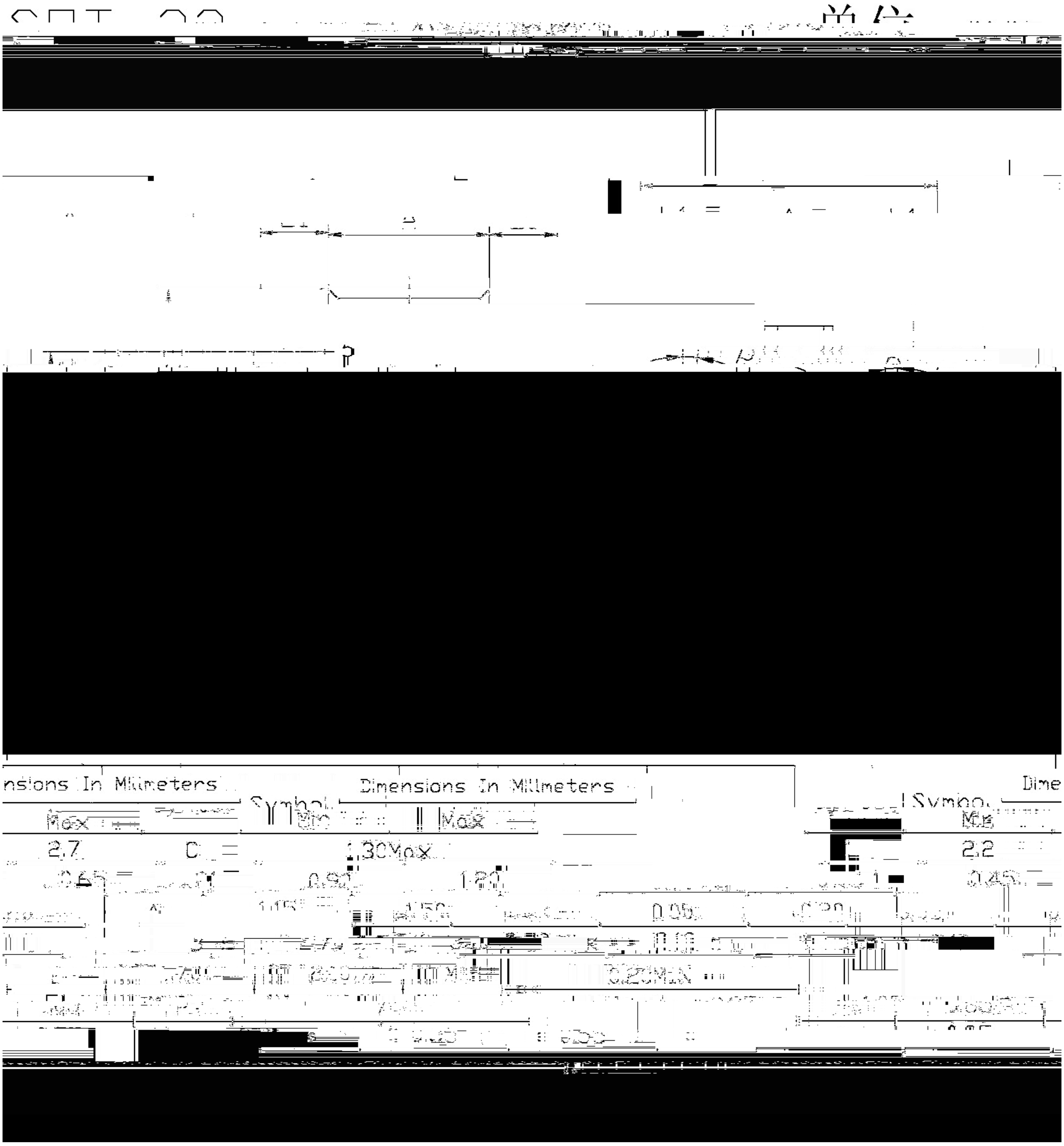
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	40	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	600	mA
Collector Power Dissipation	P_C	350	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55～150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=1.0mA I_B=0	40			V
Collector to Base Breakdown Voltage	V_{CBO}	I_C=0.1mA I_E=0	60			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=0.1mA I_C=0	6.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=60V I_E=0			50	nA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=6.0V I_C=0			50	nA
DC Current Gain	$h_{FE(1)}$	V_{CE}=1.0V I_C=150mA	100		300	
	$h_{FE(2)}$	V_{CE}=2.0V I_C=500mA	40			
	$h_{FE(3)}$	V_{CE}=1.0V I_C=10mA	80			
	$h_{FE(4)}$	V_{CE}=1.0V I_C=1.0mA	40			
	$h_{FE(5)}$	V_{CE}=1.0V I_C=0.1mA	20			
Collector-Emitter Saturation Voltage	$V_{CE(sat)\ (1)}$					

/ Package Dimensions



/ Marking Instructions

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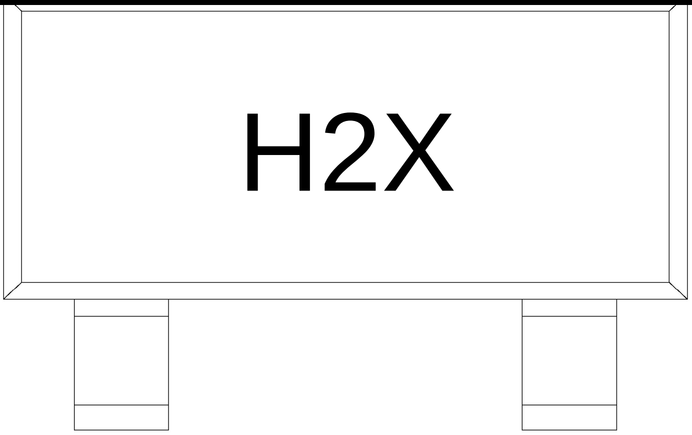

H

2X

Note:

H	Company Code
2X	Product Type Code

(　　) / Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:
1.Preheating:150~180℃, Time:60~90sec.

1 : 150 180 , 60 90sec;
2 245±5 , 5±0.5sec;